

# **N-Channel Switch**

This device is designed for analog or digital switching applications where very low On Resistance is mandatory. Sourced from Process 58. See J108 for characteristics.

# **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

357

Symbol	Parameter	Value	Units	
$V_{DG}$	Drain-Gate Voltage	25	V	
$V_{GS}$	Gate-Source Voltage	-25	V	
$I_{GF}$	Forward Gate Current	10	mA	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	-55 to +150 °C	

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

 $R_{\theta JA}$ 

Thermal Resistance, Junction to Ambient

1) These ratings are based on a maximum junction temperature of 150 degrees C.2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# Thermal Characteristics

Thermal Characteristics TA = 25°C unless otherwise noted			
Symbol	Characteristic	Max	Units
		PN5432 / 5433 / 5434	1
P <sub>D</sub>	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W

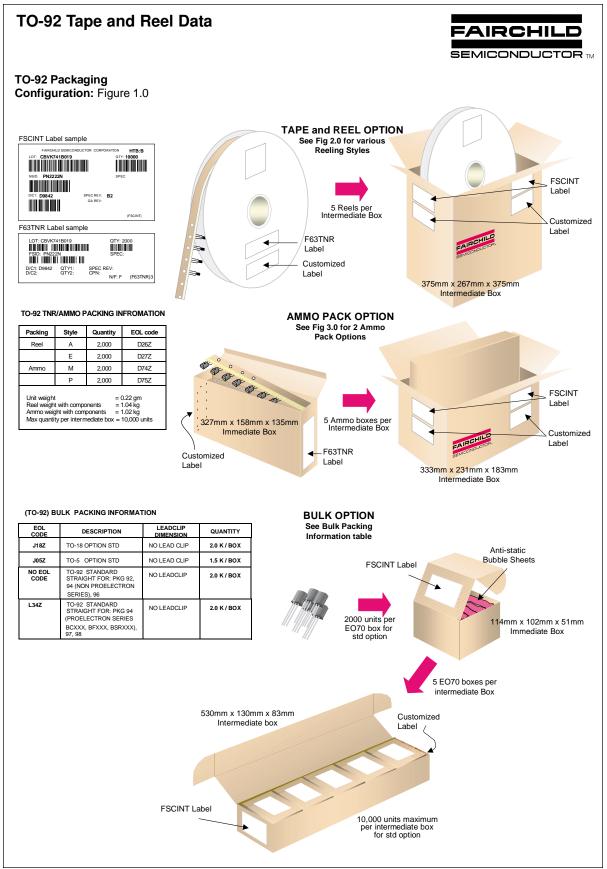
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°C/W

# N-Channel Switch (continued)

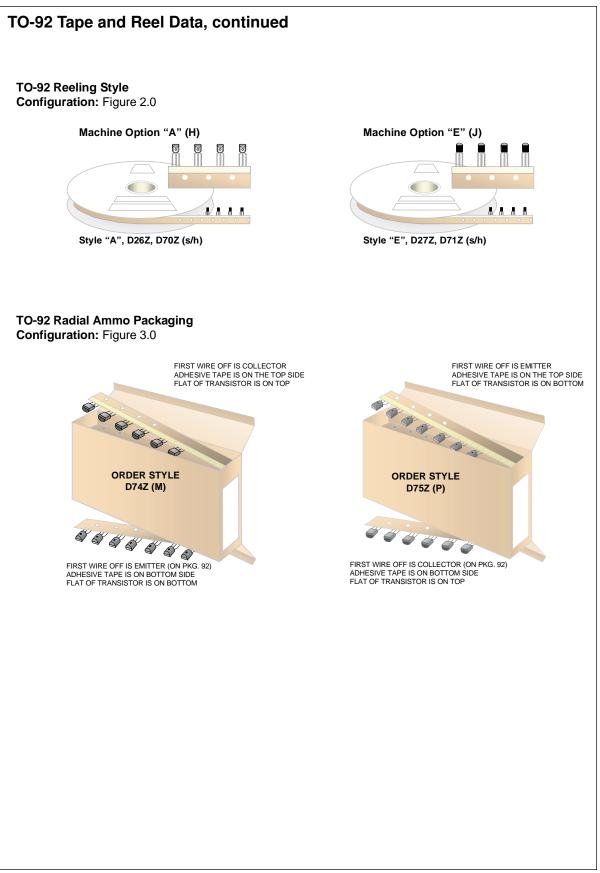
Symbol	Parameter	Test Conditions	3	Min	Max	Units
OFF CHA	ARACTERISTICS					
V <sub>(BR)GSS</sub>	Gate-Source Breakdown Voltage	$I_G = 1.0 \ \mu A, \ V_{DS} = 0$		-25		V
I <sub>GSS</sub>	Gate Reverse Current	$V_{GS} = 15 V, V_{DS} = 0$ $V_{GS} = 15 V, V_{DS} = 0, T_A = 150$	) °C		-200 -200	pA nA
I <sub>D(off)</sub>	Drain Cutoff Leakage Voltage	$\begin{array}{c c} V_{GS} = 15 \ V, \ V_{DS} = 0, \ T_A = 150 \\ \hline V_{GS} = 10 \ V, \ V_{DS} = 5.0 \ V \\ V_{GS} = 10 \ V, \ V_{DS} = 5.0 \ V, \\ T_A = 150 \ ^\circ C \end{array}$			-200 -200	pA nA
V <sub>GS(off)</sub>	Gate-Source Cutoff Voltage	$V_{DS} = 5.0 \text{ V}, \text{ I}_{D} = 3.0 \text{ nA}$	5432 5433	-4.0 -3.0	-10 -9.0	V V
			5434	-1.0	-4.0	V
ON CHAF	RACTERISTICS					<u>.</u>
I <sub>DSS</sub>	Zero-Gate Voltage Drain Current*	$V_{DS} = 15 V, V_{GS} = 0$	5432	150		mA
			5433 5434	100 30		mA mA
V <sub>DS(on)</sub>	Drain-Source On Voltage	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0	5432	00	50	mV
00(01)			5433		70	mV
			5434		100	mV
r <sub>DS(on)</sub>	Drain-Source On Resistance	$I_{D} = 10 \text{ mA}, V_{GS} = 0$	5432 5433	2.0	5.0 7.0	Ω
			5433 5434		10	Ω Ω
		$I_D = 0, V_{GS} = 0, f = 1.0 \text{ kHz}$	••••			
			5432	2.0	5.0	Ω
			5433 5434		7.0 10	Ω Ω
SMALL S	IGNAL CHARACTERISTICS				<u> </u>	32
C <sub>iss</sub>	Input Capacitance	$V_{\text{DS}}$ = 0 , $V_{\text{GS}}$ = 10 V, f = 1.0 MHz			30	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	$V_{DS} = 0$ , $V_{GS} = 10$ V, f = 1.0	MHz		15	pF
	NG CHARACTERISTICS Delay Time				4.0	
t <sub>d</sub>		$V_{DD} = 1.5 V, V_{GS(on)} = 0,$				ns
t <sub>r</sub>	Rise Time	$I_{D(on)} = 10 \text{ mA}$			1.0	ns
ts	Storage Time	$V_{GS(off)} = 12 V,$	E 420		6.0	ns
		$V_{DS(on)} = 50 \text{ mV}$ $V_{DS(on)} = 70 \text{ mV}$	5432 5433		6.0	ns
		VDS(0II) = 70 IIIV			6.0	ns
		$V_{DS(on)} = 100 \text{ mV}$	5434		0.0	

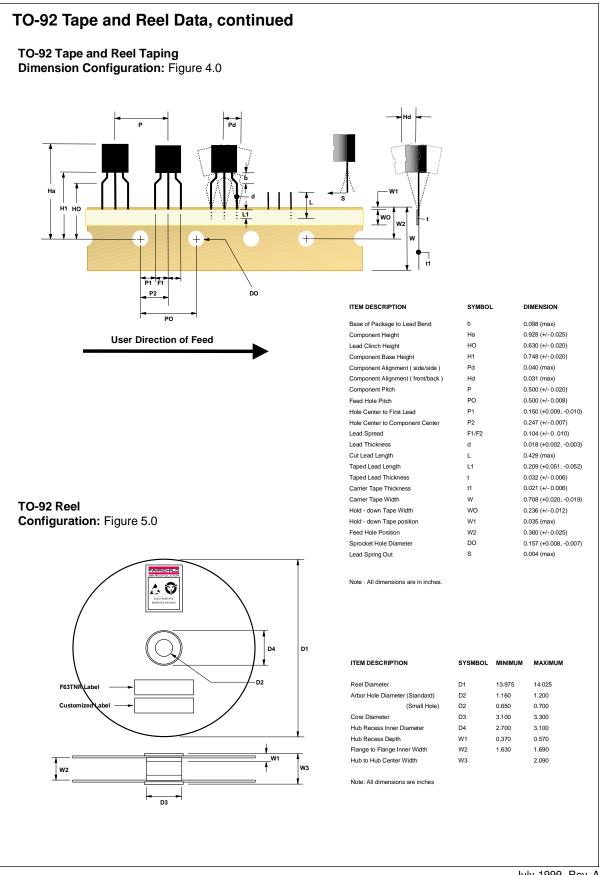
PN5432 / PN5433 / PN5434



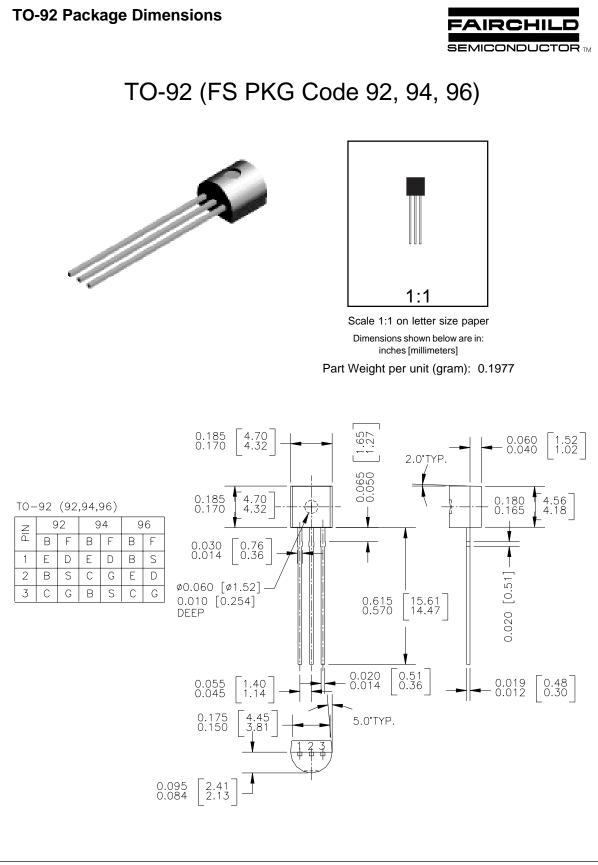
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